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NEGATIVE RESIST NR7-1000PY

Description

- Negative Resist NR7-1000PY is a negative tone photoresist designed for 365nm wavelength exposure using tools such as wafer steppers, scanning projection aligners, proximity printers and contact printers.
- After resist development NR7-1000PY exhibits a negative-sloping resist sidewall profile, which facilitates a simple resist lift-off process.
- These are the advantages of NR7-1000PY over other resists:
 - superior resolution capability of less than 0.5 μ m
 - fast develop time
 - easy adjustment of the degree of resist undercut as a function of exposure energy
 - superior temperature resistance of up to 180°C
 - superior selectivity in RIE process
 - easy resist removal in Resist Remover RR4
 - shelf life exceeding 3 years at room temperature storage.
- The formulation and processing of NR7-1000PY were designed with regard to occupational and environmental safety. The principal solvent in NR7-1000PY is cyclohexanone and development of NR7-1000PY is accomplished in a basic water solution.

Properties

♦	Solids content (%) Principal solvent	19-23 cyclohexanone
•	Appearance	light yellow liquid
•	Coating characteristic	very uniform, striation free
•	Film thickness after 150°C hotplate bake for 60 s	
	Coating spin speed, 40 s spin (rpm):	(nm)
	800	1900-2100
	2000	1170-1290
	3000	950-1050
	4000	817-903
	5000	712-788
٠	Sensitivity at 366 nm exposure wavelength (mJ/cm² for 1 µm thick film)	390

• Guaranteed shelf life at 25°C storage (years)

Processing

- 1. Application of resist by spin coating at selected spin speed for 40 s.
- 2. 150°C hotplate bake for 60 s. (softbake)
- 3. Resist exposure with a tool emitting 365 nm wavelength.
- 4. 100°C hotplate bake for 60 s. (post-exposure bake)
- 5. Resist development in Resist Developer RD6 by spray or immersion. Development time for 1 μ m thick film, for example, is 10 s. To increase development time to 50 s combine RD6/water 3:1.
- 6. Resist rinse in deionized water until water resistivity reaches prescribed limit.
- 7. Drying of resist.
- 8. Removal of resist in Resist Remover RR4 or in acetone.

The above procedure refers to substrates, which are good conductors of heat such as silicon, GaAs etc. Bake times need to be increased 3.5 times for substrates, which are poor conductors of heat such as glass.

Handling Precautions

Negative Resist NR7-1000PY is a flammable liquid. Handle it with care. Keep it away from heat, sparks and flames. Use adequate ventilation. It may be harmful if swallowed or touched. Avoid contact with liquid, vapor or spray mist. Wear chemical goggles, rubber gloves and protective coating.